

AMENDMENTS TO THE CLAIMS

1. (currently amended) A composition suitable for use as a planarizing underlayer in a multilayer lithographic process, said composition comprising:
 - (a) a polymer containing:
 - (i) epoxy moieties,
 - (ii) saturated fused-polycyclic hydrocarbon moieties,
 - (iii) aromatic moieties, and
 - (iv) fluorine-containing moieties, and
 - (b) an acid generator.
2. (previously presented) The composition of claim 1 wherein said epoxy moieties are pendant from acrylate monomers, said monomers forming at least a portion of said polymer.
3. (currently amended) The composition of claim 1 wherein said fused-polycyclic hydrocarbon moieties are pendant from acrylate monomers, said monomers forming at least a portion of said polymer.
4. (currently amended) The composition of claim 1 wherein said fused-polycyclic hydrocarbon moieties are located in a backbone portion of said polymer.
5. (original) The composition of claim 1 wherein said aromatic moieties are pendant from an ethylenic monomer, said monomer forming at least a portion of said polymer.
6. (original) The composition of claim 5 wherein said aromatic moieties are selected from the group consisting of phenyl and phenol.

7. (currently amended) The composition of claim 1 wherein said polymer contains acrylate monomers having both a ~~fused~~-polycyclic hydrocarbon moiety and an epoxy moiety pendant from said monomer.
8. (original) The composition of claim 1 wherein said acid generator is a thermally activated acid generator.
9. (canceled)
10. (original) The composition of claim 1 wherein said composition consists essentially of components (a) and (b).
11. (currently amended) A lithographic structure on a substrate, said structure comprising:
- (a) a planarizing underlayer comprising:
 - a polymer containing:
 - (i) epoxy moieties,
 - (ii) saturated ~~fused~~-polycyclic hydrocarbon moieties,
 - (iii) aromatic moieties, and
 - an acid generator.
 - (b) a radiation-sensitive imaging layer over said planarizing underlayer.
12. (canceled)
13. (original) The structure of claim 11 wherein said imaging layer is a silicon-containing resist.
- 14-20. (canceled)
